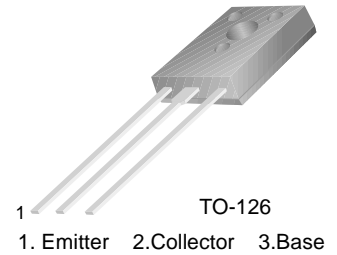


APPLICATION: High - Voltage, High - Speed Power Switching Applications.

MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT	
Collector-base voltage	VCBO	700	V	
Collector-emitter voltage	VCEO	400	V	
Emitter-base voltage	VEBO	9	V	
Collector current	IC	1.5	A	
Base current	IB	0.75	A	
Collector Power Dissipation	Pd	(Tc=25°C)	40	W
		(Ta=25°C)	1.25	
Junction Temperature	Tj	150	°C	
Storage Temperature Range	Tstg	-55-150	°C	



ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	TEST CONDITION	RATING			UNIT
			MIN.	TYP.	MAX.	
DC Current Gain	h _{FE}	V _{ce} =10 V, I _c =0.5A	8		40	β
Collector-Base Breakdown Voltage	BV _{cb0}	I _c =1 mA, I _e =0	700			V
Collector-Emitter Breakdown Voltage	BV _{ceo}	I _c =10 mA, I _b =0	400			V
Emitter-Base Breakdown Voltage	BV _{eb0}	I _e =1 mA, I _c =0	9			V
Collector Cut-off Current	I _{cbo}	V _{cb} =700 V, I _e =0			0.1	mA
Emitter Cut-off Current	I _{ebo}	V _{eb} =9 V, I _c =0			0.05	mA
Collector-Emitter Saturation Voltage	V _{ce(sat)}	I _c =1.0A, I _b =0.25A			1.0	V
Base-Emitter Saturation Voltage	V _{be(sat)}	I _c =1.0A, I _b =0.25A			1.2	V
Gain bandwidth product	f _T	V _{ce} =10V, I _c =500mA, f=1.0MHz	4			MHz
Turn on Time	t _{on}	V _{ce} =10V, I _c =2A, I _{B1} =I _{B2} =400mA			1	μs
Storage Time	t _s				4.0	μs
Fall Time	t _f				0.7	μs

h_{FE} Classification And Marking

Mark

Classification

A B C

Hfe 8-20 15-30 25-40